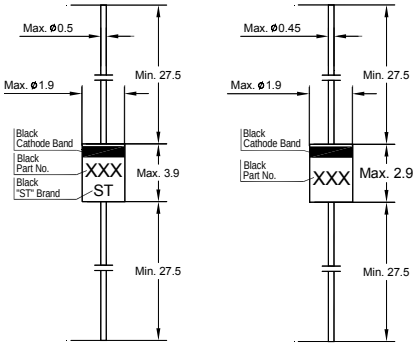
# 1N4149...1N4454

## Silicon Epitaxial Planar Switching Diode

for general purpose and switching




Glass Case DO-35
Dimensions in mm

Glass Case DO-34
Dimensions in mm

**Absolute Maximum Ratings and Characteristics** ($T_a$ = 25 °C unless otherwise specified.)

| Type | Peak Reverse Voltage | Max. Average Rectified Current | Max. Power Dissipation at 25 °C | Max. Junction Temp. | Max. Forward Voltage | | Max. Reverse Current | | Max. Reverse Recovery Time | |
|---|---|---|---|---|---|---|---|---|---|---|
| | $V_{RM}$ (V) | $I_{F(AV)}$ (mA) | $P_{tot}$ (mW) [2] | $T_j$ (°C) | $V_F$ (V) | at $I_F$ (mA) | $I_R$ (nA) | at $V_R$ (V) | $t_{rr}$ (ns) | Conditions |
| 1N4149 [1] | 100 | 150 | 500 | 200 | 1 | 10 | 25 | 20 | 4 | $I_F$ = 10 mA, $V_R$ = 6 V, $R_L$ = 100 Ω, to $I_R$ = 1 mA |
| 1N4151 | 75 | 150 | 500 | 200 | 1 | 50 | 50 | 50 | 2 | $I_F$ = 10 mA, $V_R$ = 6 V, $R_L$ = 100 Ω, to $I_R$ = 1 mA |
| 1N4152 | 40 | 150 | 400 | 175 | 0.55 | 0.1 | 50 | 30 | 2 | $I_F$ = 10 mA, $V_R$ = 6 V, $R_L$ = 100 Ω, to $I_R$ = 1 mA |
| 1N4154 | 35 | 150 | 500 | 200 | 1 | 30 | 100 | 25 | 2 | $I_F$ = 10 mA, $V_R$ = 6V, $R_L$ = 100 Ω, to $I_R$ = 1 mA |
| 1N4447 [1] | 100 | 150 | 500 | 200 | 1 | 20 | 25 | 20 | 4 | $I_F$ = 10 mA, $V_R$ = 6 V, $R_L$ = 100 Ω, to $I_R$ = 1 mA |
| 1N4449 [1] | 100 | 150 | 500 | 200 | 1 | 30 | 25 | 20 | 4 | $I_F$ = 10 mA, $V_R$ = 6 V, $R_L$ = 100 Ω, to $I_R$ = 1 mA |
| 1N4450 | 40 | 150 | 400 | 175 | 0.54 | 0.5 | 50 | 30 | 4 | $I_F$ = $I_R$ = 10 mA , to $I_R$ = 1 mA |
| 1N4451 | 40 | 150 | 400 | 175 | 0.5 | 0.1 | 50 | 30 | 10 | $I_F$ = $I_R$ = 10 mA , to $I_R$ = 1 mA |
| 1N4453 | 30 | 150 | 400 | 175 | 0.55 | 0.01 | 50 | 20 | - | - |
| 1N4454 | 75 | 150 | 400 | 175 | 1 | 10 | 100 | 50 | 4 | $I_F$ = $I_R$ = 10 mA , to $I_R$ = 1 mA |

[1] These diodes are also available in glass case DO-34. Parameter for diodes in case DO-34: $P_{tot}$ = 300 mW, $T_j$ = 175 °C
[2] Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature.